

Silicon PIN Diode

- RF switch, RF attenuator for frequencies above 10 MHz
- Low distortion faktor
- Long-term stability of electrical characteristics
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



BAR14-1

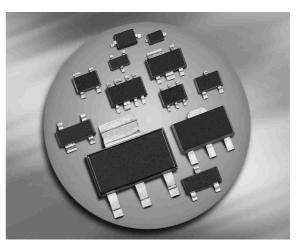




BAR15-1



BAR16-1



BAR61



Туре	Package	Configuration	L _S (nH)	Marking
BAR14-1	SOT23	series	1.8	L7s
BAR15-1	SOT23	common cathode	1.8	L8s
BAR16-1	SOT23	common anode	1.8	L9s
BAR61	SOT143	PI element	2	61s

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit V	
Diode reverse voltage	V _R	100		
Forward current	I _F	140	mA	
Total power dissipation	P _{tot}	250	mW	
$T_{\rm S} \le 65^{\circ}{\rm C}$				
Junction temperature	Ti	150	°C	
Operating temperature range	T _{op}	-55 125		
Storage temperature	T _{stg}	-55 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 340	K/W

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance



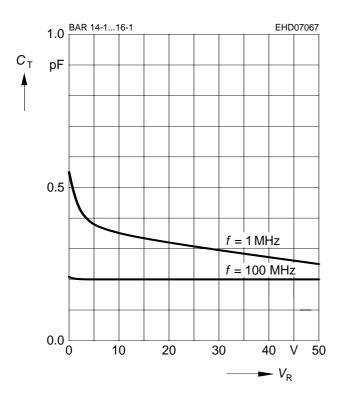
Parameter	Symbol	Values			Unit
		min.	typ.	max.	1
DC Characteristics					
Reverse current	I _R				nA
V _R = 50 V		-	-	100	
<i>V</i> _R = 100 V		-	-	1000	
Forward voltage	V _F	-	1.05	1.25	V
<i>I</i> _F = 100 mA					
AC Characteristics					
Diode capacitance	CT				pF
V _R = 0 V, <i>f</i> = 100 MHz		-	0.2	0.5	
V _R = 50 V, <i>f</i> = 1 MHz		-	0.25	0.5	
Zero bias conductance	g _P	-	50	100	μS
V _R = 0 V, <i>f</i> = 100 MHz					
Forward resistance	r _f				Ω
<i>I</i> _F = 0.01 mA, <i>f</i> = 100 MHz		-	2600	4200	
<i>I</i> _F = 0.1 mA, <i>f</i> = 100 MHz		300	470	-	
<i>I</i> _F = 1 mA, <i>f</i> = 100 MHz		35	55	85	
<i>I</i> _F = 10 mA, <i>f</i> = 100 MHz		5.5	8	12	
Charge carrier life time	τ _{rr}	700	1000	-	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 6 mA, measured at $I_{\rm R}$ = 3 mA,					
R _L = 100 Ω					
I-region width	W	-	146	-	μm

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified



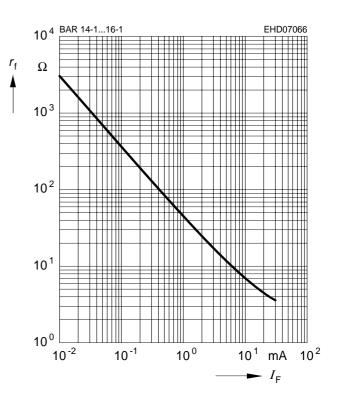
Diode capacitance $C_{T} = f(V_{R})$

f = Parameter



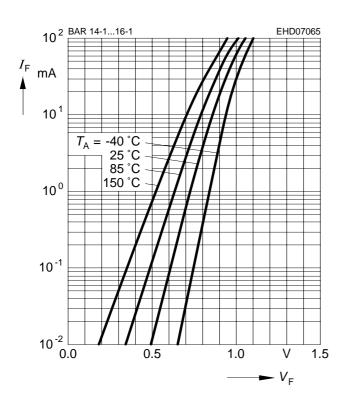
Forward resistance $r_{\rm f} = f (I_{\rm F})$

f = 100 MHz

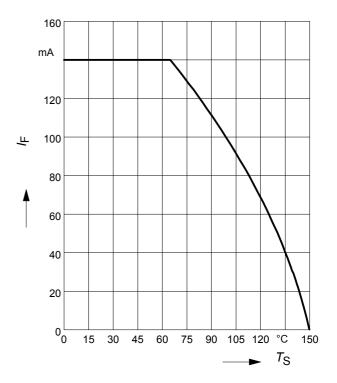


Forward current $I_{\rm F}$ = $f(V_{\rm F})$

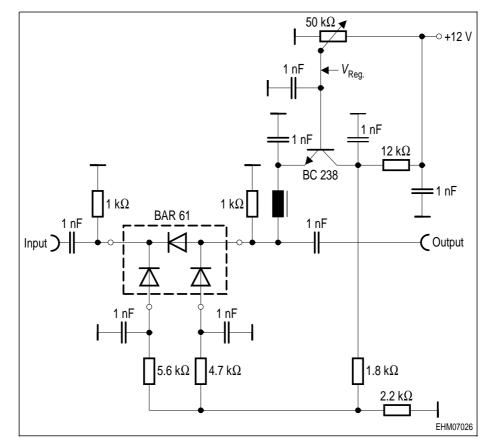
 $T_A = 25^{\circ}C$



Forward current $I_F = f(T_S)$ BAR14-1, BAR15-1, BAR16-1

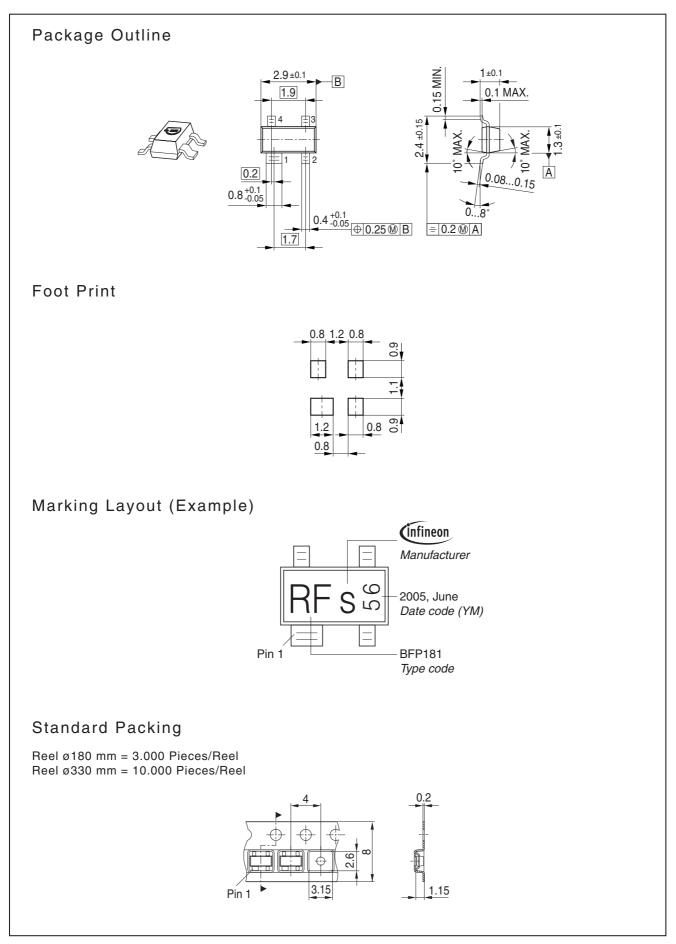




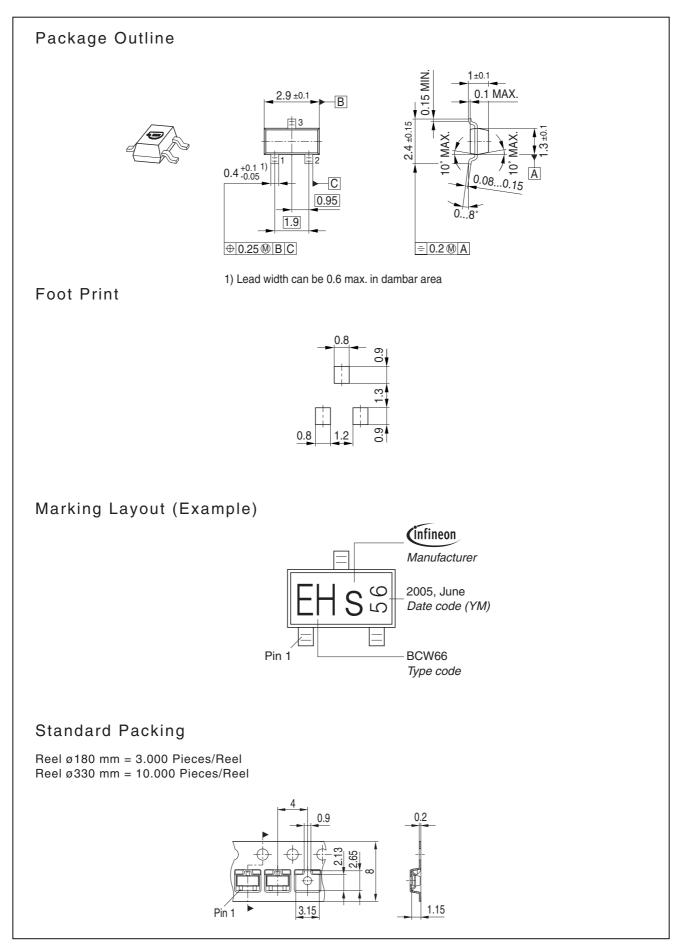


Application circuit for attenuation networks with diode BAR61













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